

IMPORTANT: Besides your **calculator** and the sheets you use for calculations you are only allowed to have an A4 sized “**copy sheet**” during this exam. Notes, problems and alike are not permitted. **Please submit your “copy sheet” along with your solutions.** You may get your “copy sheet” back after your solutions have been graded. **Do not forget to write down units and convert units carefully! Cell phones are not allowed and should be placed on the front desk before the exam.**

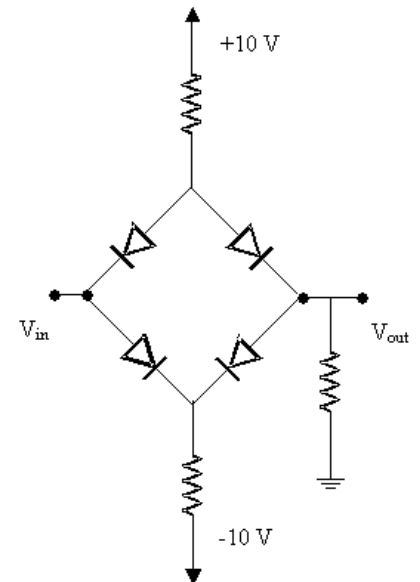
EHB222E INTRODUCTION TO ELECTRONICS (21124)

Midterm Exam #1 ✍️ **19 March 2018** ⌚ **9.30-11.30**

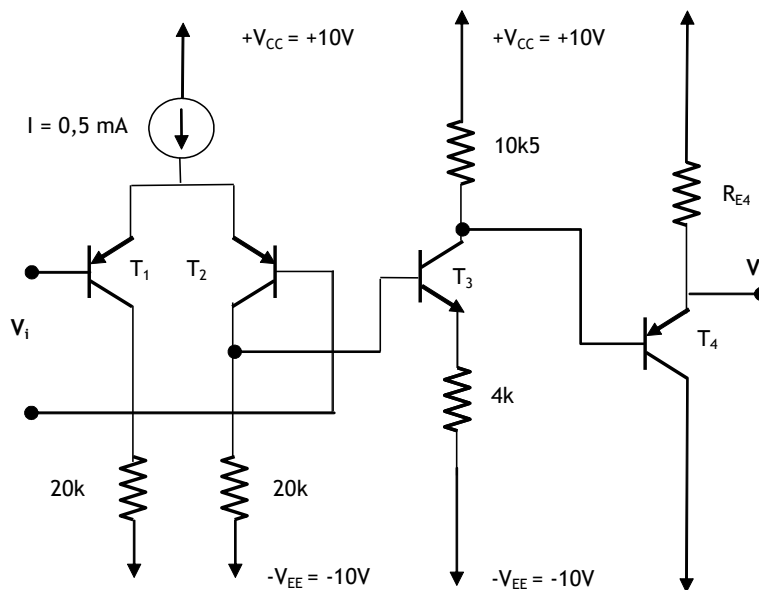
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EEF 5205

1. Compare and contrast conductors vs. semi-conductors. State similarities and differences. (10 p BONUS!)
2. Assume you have a diode made of n- and p-typed doped silicon with the following parameters $N_D = 10^{16} \text{ 1/cm}^3$ and $N_A = 10^{17} \text{ 1/cm}^3$. You also know $L_n = 10 \text{ }\mu\text{m}$, $L_p = 5 \text{ }\mu\text{m}$, $\mu_n = 1350 \text{ cm}^2/\text{Vs}$, $\mu_p = 480 \text{ cm}^2/\text{Vs}$, $n_i = 1.5 \cdot 10^{10} \text{ 1/cm}^3$, $q = 1.602 \cdot 10^{-19} \text{ C}$, $\epsilon_r = 12$, $\epsilon_o = 8.85 \cdot 10^{-12} \text{ F/m}$, $V_T = 25 \text{ mV}$
 - a. For the dark current (I_o) to be under 100 fA how large should the junction area A be in mm^2 ? (10)
 - b. If you cannot find A above, assume $0,5 \text{ mm}^2$ and calculate specific conductances of n and p type doped regions. (10)
 - c. Find depletion range width and junction capacitance in unbiased state. (10 puan)
3. For the circuit shown on the right sketch V_{out} as a function of V_{in} for V_{in} : -10 V to +10 V assuming all three resistors are 10k and the voltage drop across conducting diodes are constant at 0,6 V. (30 points)
HINT: Analyze the circuit first at $V_{in} = 0\text{V}$; then at +10 V and -10 V, and finally at values in between.
4. Study DC characteristics of the 3-stage BJT amplifier circuit with $|V_{BE}| = 0,6 \text{ V}$, $h_{FE} = 100$ for all four transistors.
 - a. Design a current source that will provide 0,5 mA biasing current to the differential stage. (10 p)



- b. How should R_{E4} be chosen, such that, waveform distortion at the output is symmetrical, that is, $V_o = 0\text{V}$? If you cannot find take $I_{C3} = 1 \text{ mA}$. (30p)



GOOD LUCK

SOLUTIONS:

2. $D_{p/n} = V_T \cdot \mu_{p/n}$ ' thus $D_p = 12 \text{ cm}^2/\text{s}$ and $D_n = 33.8 \text{ cm}^2/\text{s}$

a. $I_o = A \cdot q \cdot n_i^2 \cdot \left[\frac{D_p}{L_p N_D} + \frac{D_n}{L_n N_A} \right]$ thus if $I_o < 100 \text{ fA}$ for $A < 1,01 \text{ mm}^2$.

Thus I choose $A = 1 \text{ mm}^2$.

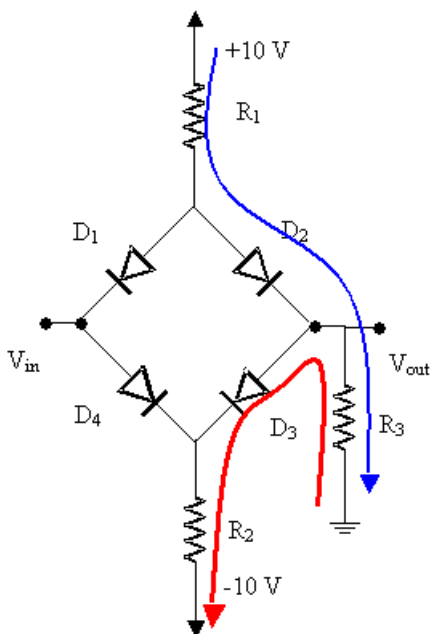
b. $\sigma_p = q \cdot \left(\frac{n_i^2}{N_A} \mu_n + N_A \mu_p \right); \quad \sigma_n = q \cdot \left(N_D \mu_n + \frac{n_i^2}{N_D} \mu_p \right)$

Thus $\sigma_p = 7,69 \text{ 1}/(\Omega \text{ cm})$ $\sigma_n = 2,16 \text{ 1}/(\Omega \text{ cm})$.

c. $V_B = -V_T \cdot \ln \left(\frac{n_i^2}{N_A \cdot N_D} \right)$ thus $V_B = 728 \text{ mV}$ and $w = \sqrt{\frac{2 \cdot \epsilon_o \cdot \epsilon_r \cdot V_B}{q \cdot \left[\frac{1}{N_A} + \frac{1}{N_D} \right]}}$ thus

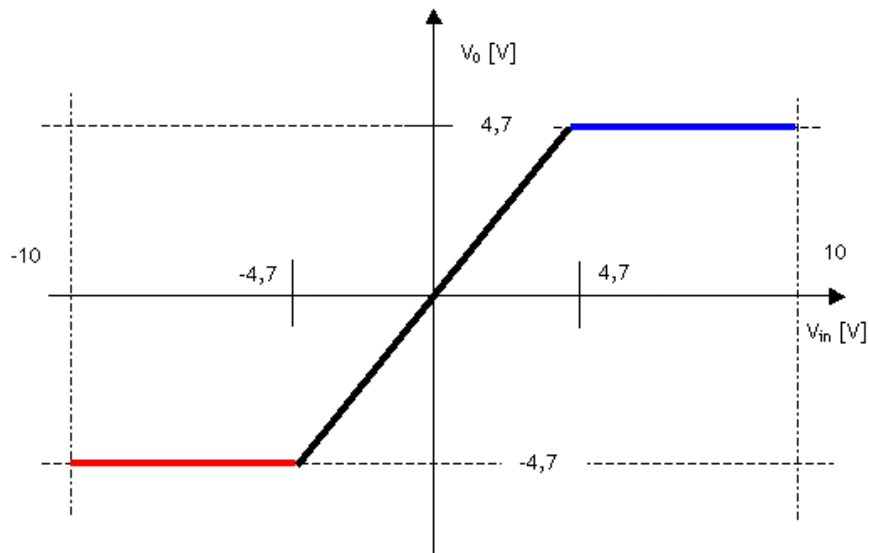
$w_{\text{dep}} = 3,26 \text{ }\mu\text{m}$ and $C = \epsilon_o \cdot \epsilon_r \cdot \frac{A}{w} \text{ C} = 326 \text{ pF}$

3. Assume there is no V_{in} . $V_{out} = 0\text{V}$ because of the symmetry of the circuit, and because all diodes are conducting. This is the same as $V_{in} = 0\text{V}$. Now assume $V_{in} = +10\text{V}$. We can easily see that D_1 and D_3 are reverse biased because most of the voltage drop from $+10\text{V}$ to -10V is over the resistors R_1 and R_2 . In other words, the anode of D_1 is much less than $+10\text{V}$ whereas the cathode is at $+10\text{V}$ (reverse bias). Also, D_4 is conducting, thus, the cathode of D_3 is at $9,4\text{V}$ whereas the anode of D_3 is much less than $+9,4\text{V}$. That means current flows (a) from $+10\text{V}$ over R_1 , D_2 , and R_3 to ground (follow blue line), and (b) from V_{in} over D_4 and R_4 to -10V . Since only $0,6\text{V}$ drops on the conducting diodes $9,4\text{V}$ drops over the two resistors R_1 and R_3 . Since R_1 and R_3 have equal values, we divide the voltage drop by 2 and this is $V_{out} = 4.7\text{V}$.



Now assume $V_{in} = -10\text{V}$. Similar to the observations above, D_4 and D_2 are reverse biased because most of the voltage drop from $+10\text{V}$ to -10V is again over the resistors R_1 and R_2 . In other words, the cathode of D_4 is much higher than -10V whereas the anode is at -10V (reverse bias again). Also, D_1 is conducting, thus, the anode of D_2 is at $-9,4\text{V}$ whereas the cathode of D_2 is much higher than $-9,4\text{V}$. That means current flows (a) from the ground over R_3 , D_3 , and R_2 to -10V (follow red line), and (b) from $+10\text{V}$ over R_1 and D_1 to V_{in} . Since only $0,6\text{V}$ drops on the conducting diodes $9,4\text{V}$ drops over the two resistors R_2 and R_3 . Since R_2 and R_3 have equal values, we divide the voltage drop by 2 and this is $V_{out} = 4.7\text{V}$.

Finally, we need to consider the output for $0\text{V} \geq V_{in} \geq -10\text{V}$ and $0\text{V} \leq V_{in} \leq +10\text{V}$. One sees easily that when all the 4 diodes are conducting, the output V_{out} follows the input V_{in} because the circuit is symmetrical. When do all the 4 diodes conduct? See the sketch below....Capito????



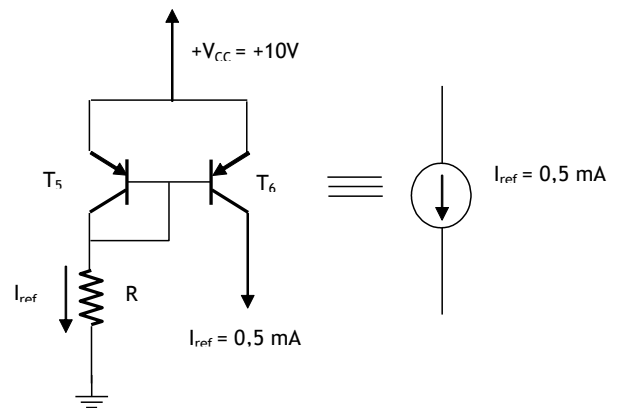
4. DC characteristics are to be studied.

- a. See the sketch below. You should calculate the value of R , and make sure T_6 operates in active mode.

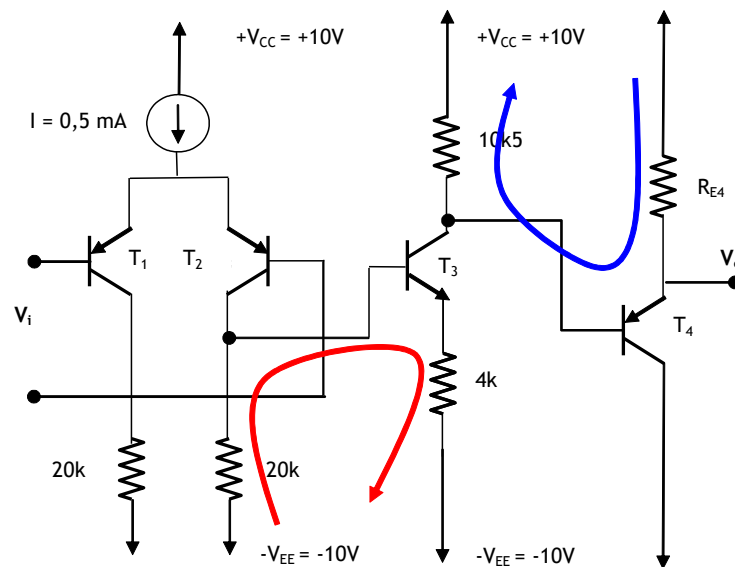
Without neglecting the base currents of the differential stage, for $V_i = 0$

$$I_{C1} = I_{C2} = \frac{h_{FE}}{h_{FE} + 1} \cdot \frac{0,5mA}{2}$$

$$I_{C1} = I_{C2} = \underline{\underline{0,248mA}}$$



- b. Following the red loop $-(I_{C2} - I_{B3})20k + V_{BE3} + (h_{FE} + 1)I_{B3}4k = 0$



$$I_{C3} = h_{FE} \frac{20k * I_{C2} - V_{BE3}}{(h_{FE} + 1)4k + 20k} = 100 \frac{20k * 0,248mA - 0,6V}{(100 + 1)4k + 20k} = \underline{\underline{1,028mA}}$$

Following the blue loop and recalling that waveform distortion at the output should be minimum and symmetrical, i.e., $V_o = 0\text{ V}$

$$(h_{FE} + 1)I_{B3}R_{E4} + V_{EB4} - (I_{C3} - I_{B4})10k5 = 0, \quad \text{with} \quad (h_{FE} + 1)I_{B4}R_{E4} = 10V$$

$$10V + V_{EB4} - (I_{C3} - I_{B4})10k5 = 10V + 0,6V - (1,028\text{ mA} - I_{B4})10k5 = 0$$

$$I_{C4} = h_{FE} \left[1,028\text{ mA} - \frac{10,6V}{10k5} \right] = \underline{\underline{1,87\text{ mA}}} \text{ and } R_{E4} = \frac{10V}{(h_{FE} + 1)I_{B4}} = \underline{\underline{5k27}}$$